CLAIMS

What is claimed is:

1. A method of etching patterned features into at least one conductive layer, at least one dielectric layer, and into a silicon substrate through a patterned mask, comprising:

a) loading a silicon wafer into a process chamber, wherein the at least one conductive layer and the at least one dielectric layer is disposed over the silicon wafer;

b) etching at least one conductive layer through the patterned mask, comprising

flowing a conductive layer etch gas into the process chamber;

forming a plasma from the conductive layer etch gas;

etching the at least one conductive layer with the plasma formed from the conductive layer etch gas such that the at least one conductive layer is patterned to have the features therein; and

stopping the conductive layer etch gas flow;

c) etching at least one dielectric layer through the patterned mask, comprising:

flowing a dielectric layer etch gas into the process chamber;

forming a plasma from the dielectric layer etch gas;

etching the at least one dielectric layer with the plasma formed from the dielectric layer etch gas such that the at least one dielectric layer is patterned to have the features therein; and

stopping the dielectric layer etch gas flow;

d) etching the silicon layer through the patterned mask, the at least one patterned conductive layer, and the at least one patterned dielectric layer, comprising:

flowing a silicon etch gas into the chamber;

forming a plasma from the silicon etch gas;

etching into the silicon wafer with the plasma formed from the silicon etch gas; and

stopping the silicon etch gas flow; and